

# PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APM-AAM/09/4449 Notification Date 04/27/2009

Transfer of HCMOSTD process logic devices from CSMC (China) to AMK6 (ST in-house plant)

#### **Table 1. Change Implementation Schedule**

Forecasted implementation date for change	18-Jun-2009
Forecasted availabillity date of samples for customer	20-Apr-2009
Forecasted date for <b>STMicroelectronics</b> change Qualification Plan results availability	20-Apr-2009
Estimated date of changed product first shipment	27-Jul-2009

### **Table 2. Change Identification**

Product Identification (Product Family/Commercial Product)	see attached list
Type of change	Waferfab location change
Reason for change	Higher manufacturing flexibility.
Description of the change	Moving of HCMOS4 Diffusion Line from CSMC (Subcontractor in China) to STMicroelectronics in-house diffusion plant, AMK6, in Singapore.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	See "V6" as Wafer code in traceability code
Manufacturing Location(s)	

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Тэ	hla	2	lict	∧f	Attac	hments	
	DIE	J.	LISL	UI.	Allau		

Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN APM-AAM/09/4449
Please sign and return to STMicroelectronics Sales Office	Notification Date 04/27/2009
□ Qualification Plan Denied	Name:
□ Qualification Plan Approved	Title:
	Company:
□ Change Denied	Date:
□ Change Approved	Signature:
Remark	
1	

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# **DOCUMENT APPROVAL**

Name	Function	
Noviello, Giuseppe	Division Marketing Manager	
Russo, Biagio	Division Product Manager	
Calderoni, Michele	Division Q.A. Manager	

**A7**/.

Report ID: REL6043-286W08

# **Reliability Report**

HCMOS4 TX - AMK6- Technology
Process Qualification

Test Vehicle: 74LX1G04BJR - Flip Chip 4 Package

General Information

Product Line EF04

The 74LX1G04 is a low voltage CMOS SINGLE

**Product Description** 

INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring

C2MOS technology.

Commercial Product 74LX1G04BJR

Product Group Advanced and Analog Logic

Product Division IMS - APM GROUP

Package Description Flip Chip 4

500UM PITCH ,300UM BALL

Silicon Process Technology HCMOS4 TX

Locations

Wafer fabrication location Ang Mo Kio (AMK6)

UBM at AMK5,
Assembly plant location Bumping and testing

at SHENZEN

Final test plant location SHENZEN

#### **DOCUMENT HISTORY**

Version	Date	Pages	Author	Comment
0.1	October-08	7	Giovanni Presti Stefania Motta	Original document Catania Q & Reliability
4				
4				

Reliability is the attitude of element to satisfy required function in fixed conditions during established time.

Version 0.1 Page 1/9

Report ID: REL6043-286W08

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test **methods**.

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Version 0.1 Page 2/9

# Report ID: REL6043-286W08

### TABLE OF CONTENTS

1	RELIABILITY EVALUATION OVERVIEW
	1.1 OBJECTIVES
	1.2 CONCLUSION
2	DEVICE CHARACTERISTICS4
	2.1 DEVICE DESCRIPTION
	2.1.1 Wafer fabrication information
	2.1.2 Assembly information
3	RELIABILITY TESTS RESULTS
	3.1 RELIABILITY TEST PLAN AND RESULTS SUMMARY
	3.2 DIE ORIENTED TESTS
	3.3 PACKAGE ORIENTED TESTS
	APPLICABLE AND REFERENCE DOCUMENTS
5	GLOSSARY
6	ANNEXES

Version 0.1 Page 3/9

Report ID: REL6043-286W08

### 1 RELIABILITY EVALUATION OVERVIEW

### 1.1 Objectives

HCMOS4TX DIFFUSION TRANSFER FROM CARROLLTON 6" to AMK 6".

Aim of this report is to present the results of the reliability evaluations performed on 74LX1G04BJR device, used as test vehicle for Process qualification in order to qualify HCMOS4 TX technology diffused in AMK6. No changes in devices design or devices layout, no changes in devices structure, no changes in back-end operations

### 1.2 Conclusion

The final reliability results are positive.

### 2 DEVICE CHARACTERISTICS

### 2.1 Device description

The 74LX1G04 is a low voltage CMOS SINGLE INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C2MOS technology. It is ideal for 1.65 to 5.5 VCC operations and low power and low noise applications. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. Power down protection is provided on input and output and 0 to 7V can be accepted on inputs with no regard to the supply voltage. It can be interfaced to 5V signal environment for inputs in mixed 3.3/5V system. All inputs and outputs are equipped with protection circuits against static discharge.

#### 2.1.1 Wafer fabrication information

- Wafer fabrication manufacturing location: AMK6
- > Technology: HCMOS4 TX
- Die size: 0.9 x 0.9

#### 2.1.2 Assembly information

- Assembly site: UBM at AMK5, Bumping and testing at SHENZEN
- ➤ Package description: Flip Chip 4 bumps, 500um pitch ,300UM Ball

Version 0.1 Page 4/9

Report ID: REL6043-286W08

### **3 RELIABILITY TESTS RESULTS**

# 3.1 Reliability test plan and results summary

Include here the tests plan and the results summary.

#### Die oriented test

	Test short description				VIII 1000.
Test	Method Conditions		Sample Size	Duration	Results Fail/ Sample Size
нтв	High Tempe	erature Bias	A		
пь		Ta = 125℃, Vdd = 7V	77x3 Lots	1000 h	0/231
HTS High Temperature Storage					
1113		Ta = 150℃	77x3 Lots	1000 h	0/231

All samples are assembled on PCB (soldering profile according to JEDEC 020D)

#### Package oriented test

	Test short	description			
Test	Method	Conditions	Sample Size	Duration	Results Fail/ Sample Size
T.H.B.	Temperatur	e Humidity Bias			
1.11.6.		Ta=85℃ Rh=85%, Vdd= 5V	77x1 Lot	1000 h	0/77
T.C.	Thermal Cy	cle			
		TA=-40℃ TO 125℃ (1 HOUR/CYCLE)	77x1 Lot	500 cy	0/77
T.H.S.	Temperature Humidity Storage				
1.11.3.		TA=85℃ - Rh=85%	77x1 Lot	1000 h	0/77
	SMD INDU	CED STRESS			
S.M.D.		IR 3 times @ Tpeack=260℃ According to JEDEC020D	154x2 Lots 231x 1 Lot	Parameter deviation within spec. limits at end of test	Parameter deviation within spec. limits after go no go test

All samples are assembled on PCB (soldering profile according to JEDEC 020D)

#### **ESD** test

Zap circuit HBM 11-C; Zap vs. VCC, Zap vs. GND, Zap vs. I/O, Zap +, Zap -

ESD Model	Stress voltage (V)	Result
HBM	2 KV	Passed

Version 0.1 Page 5/9

Report ID: REL6043-286W08

ESD test is satisfactory.



Version 0.1 Page 6/9

Report ID: REL6043-286W08

#### Latch-Up test

L/U	Stress Condition	Result
Input and Output Injection	0mA to -500mA; 5.5V	Passed
Power Supply Over Voltage	Input set to VCC; Input set to GND	Passed

Latch-up tests are satisfactory.

### 3.2 Die oriented tests

These tests are performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and reverse biased.

The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, metal corrosion, etc

### 3.3 Package oriented tests

These tests are performed in order to check device life in various environmental conditions in an accelerated way. Detectable failure mechanisms are metal corrosion, cracking of die, and mechanical damage to the device case.

Version 0.1 Page 7/9

Report ID: REL6043-286W08

### **4 APPLICABLE AND REFERENCE DOCUMENTS**

Document reference Short description

AEC-Q100 : Stress test qualification for integrated circuits SOP 2610 : General product qualification procedure

Internal : Reliability Tests and criteria for qualifications (CORPORATE Q&R RULES)

ST specification

## **5 GLOSSARY**

HTB High Temperature Bias (Operative Life)

HTS High Temperature Storage T.H.B. Temperature Humidity Bias

T.C. Thermal Cycle

T.H.S. Temperature Humidity StorageS.M.D. Surface Mounting Device Stress

P.C.B. Printed Circuit Board

Version 0.1 Page 8/9

Report ID: REL6043-286W08

# **6 ANNEXES**



Version 0.1 Page 9/9

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